

2N5772

NPN Switching Transistor

• Sourced from process 22.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continued	300	mA
T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.

 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics				
BV _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	15		V
BV _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 100\mu A, V_{BE} = 0$	40		V
BV _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	40		V
BV _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 20V, I _E = 0		0.5	μΑ
I _{CES}	Collector Cutoff Current	$V_{CE} = 20V, V_{BE} = 0$ $V_{CE} = 20V, V_{BE} = 0, T_a = 65^{\circ}C$		0.5 3.0	μA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$		100	μΑ
On Charact	eristics *				
h _{FE}	DC Current Gain	$V_{CE} = 0.4V, I_{C} = 30mA$	30	120	
		$V_{CE} = 0.5V, I_{C} = 100mA$	25		
		$V_{CE} = 1.0V, I_{C} = 300mA$	15		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 30 \text{mA}, I_B = 3.0 \text{mA}$		0.2	V
		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		0.28	V
		$I_C = 300 \text{mA}, I_B = 3.0 \text{mA}$		0.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 30 \text{mA}, I_B = 3.0 \text{mA}$	0.73	0.95	V
		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		1.2	V
		$I_C = 300 \text{mA}, I_B = 3.0 \text{mA}$		1.7	V
Small Signa	Il Characteristics				
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0V, I_{E} = 0, f = 1MHz$		5.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{CB} = 5.0V, I_{C} = 0, f = 1MHz$		8.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 300 \text{mA}, V_{CE} = 10 \text{V}, f = 100 \text{MHz}$	3.5		

* Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$

Electrical Characteristics Ta=25°C unless otherwise noted (Continued)

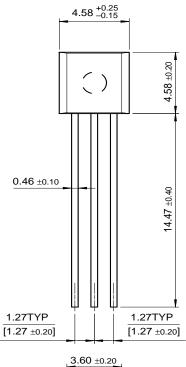
Symbol	Parameter	Test Condition	Min.	Max.	Units
Switching Characteristics					
t _s	Storage Time	I _C = 300mA, V _{CC} = 10V		20	ns
t _{on}	Turn-On Time	$I_{B1} = I_{B2} = 30 \text{mA}$		18	ns
t _{off}	Turn-Off Time			28	ns

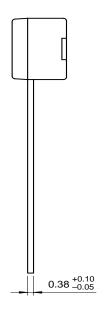
Thermal Characteristics T_a =25°C unless otherwise noted

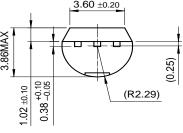
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

Package Dimensions

TO-92







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